



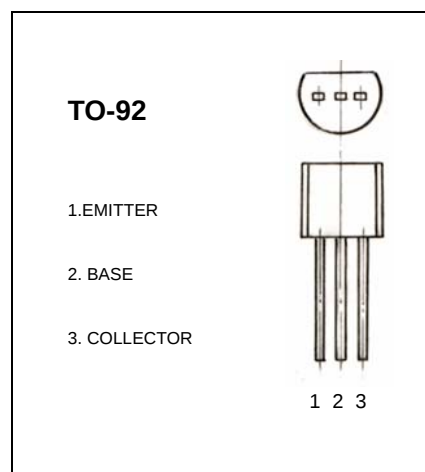
TO-92 Plastic-Encapsulate Transistors

M8550 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 625 \text{ m W}(T_{amb}=25^{\circ}\text{C})$$



MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-800	mA
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}^*$	$I_C = -0.1\text{mA}, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_B = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -5\text{mA}$	45		
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	80	400	
	$h_{FE(3)}$	$V_{CE} = -1\text{V}, I_C = -800\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f = 30\text{MHz}$	150		MHz

* Pulse Test : pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

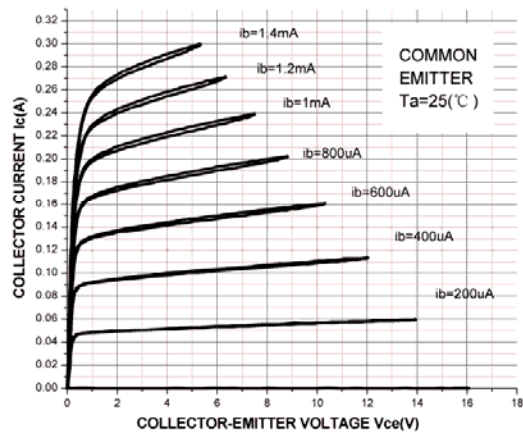
CLASSIFICATION OF $h_{FE(2)}$

Rank	B	C	D	D3
Range	80-160	120-200	160-300	300-400

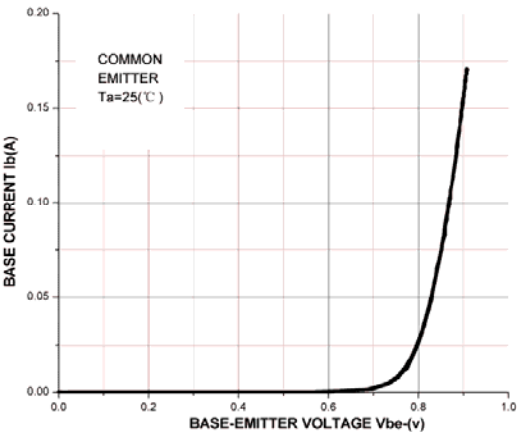
Typical Characteristics

M8550

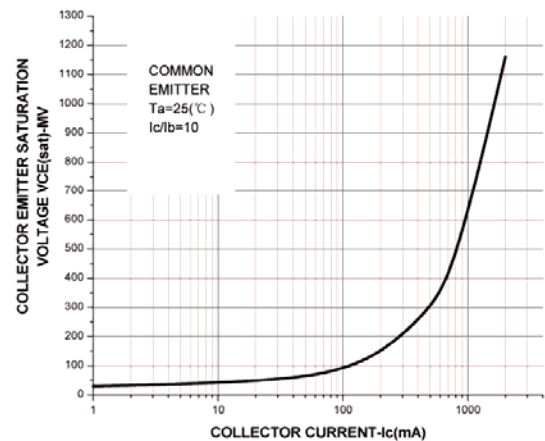
Ic-Vce



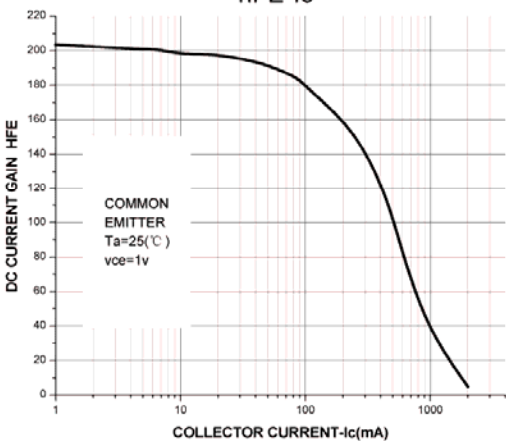
Ib-Vbe



Vcesat-Ic



hFE-Ic



Pc-Ta

